Speed Vs Area Trade of

tr = 2.2 RpCout | tf = 2.2 Rn Cout

Prise time, fall time are dependent on parasitic Capacitances and resistances.

At we increase (1) the aspect ratio (12) then Resistance (1) then, tr & to (1) decreases.

So, Mosfet is operating fastly with ten so, inorder to get faster Mosfet, we increase the area (1). Then integration density will be lever (1).

DC Current flow

There is no path Connecting from Non to ground.

If we have, path from Voo to ground then only we can say, we that anvent is flowing through the transistor,

Then the current will thow, power dissipitation will occur:

At point A, Mn is I peak.

Of and at Point B

Took

Took

Took

ON at VM.

Ipeak Too

Then both the transistors are equally Connected & they have low resistance (convent is high). And this Resistance is Connected to GNO.

1009 = Quies cent auent/ leakage auent/

IDDA + it is the static cullent flowing through the transistor even when it is not switching.

This is not Completely open CKT [even

if we don't apply i/p) because of

high resistance blue orain & Source. Because
of his flere will be some less small

leakage current. This current is known

as static current (Tooo)

as Static power = Von Tooo - static power

When the bransistors are switching, Capacitor Changes and discharges that will Contribute that will Contribute the daying and discharging currents. These awants are will contribute power i.e. Dynamic power.

Par = Voo Too = Voo (Qe) (Share Qe = Court oo)

